

## CLAIMS:

1. A method of wire bonding of a semiconductor device for resolving oxidation of copper bonding pad, the method comprising the steps of:

a wafer 1 with copper bonding pad 11 being provided;

5 covering the copper bonding pad 11 of the wafer 1 with an anti-oxidization protective film 12 which will be vaporized when heated in the course of fabricating copper bonding pad 11 of the wafer 1 to protect the copper bonding pad 11 from being oxidezed, providing a longer shelf-life; and performing wire bonding directly without requiring the removal of the  
10 protective film 12, employing mechanical energy such as ultrasonic vibration energy, pressurizing deformation energy and heat energy in the course of bonding to vaporize the protective film 12 so that the metal wire 23 and the copper bonding pad 11 form into a large area intermetallic compound layer for bonding.